

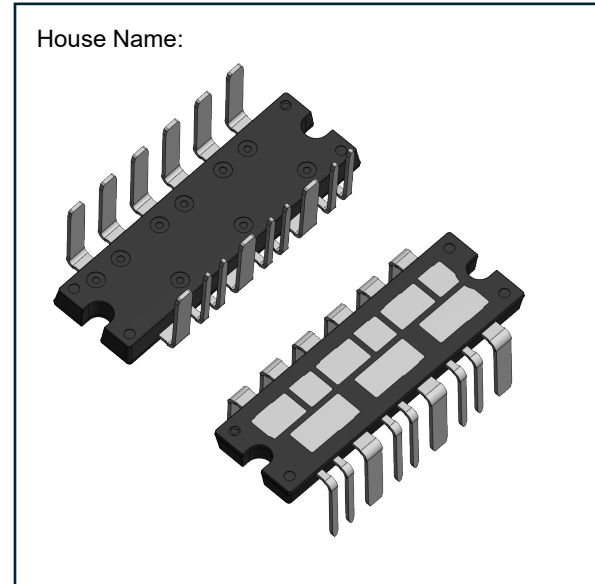
MG031AF150006A

3-phase inverter bridge

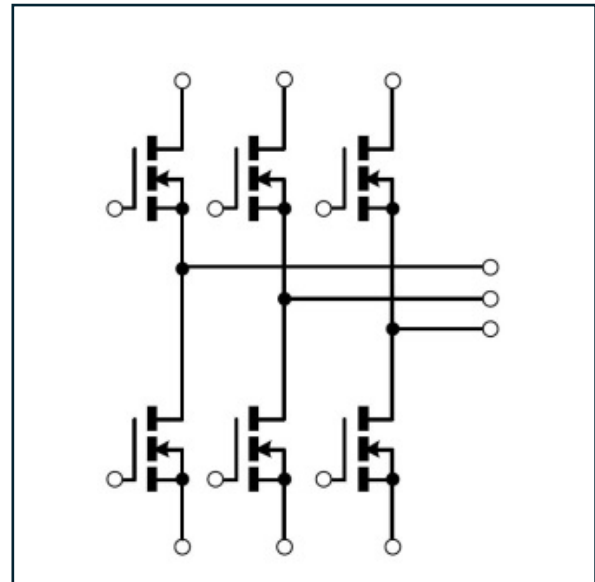
Features

- 3 phase Inverter
- Cu clips
- Compact design DIP package
- Tch=175° C guarantee
- Pb free terminal
- RoHS:Yes

Outline



Equivalent Circuit



Absolute Maximum Ratings (Tc = 25°C unless otherwise specified)

MOSFET

項目 Item	記号 Symbol	条件 Conditions	規格値 Ratings	単位 Unit
チャンネル温度 Channel temperature	Tch		175	°C
ドレイン・ソース間電圧 Drain-source voltage	V _{DSS}		60	V
ゲート・ソース間電圧 Gate-source voltage	V _{GSS}		± 20	V
ドレイン電流 (直流) Continuous drain current (DC)	I _D		150	A
ドレイン電流 (ピーク) Continuous drain current (Peak)	I _{DP}	パルス幅 10μs, Duty = 1/100 Pulse width 10μs, Duty = 1/100	600	A
全損失 Total power dissipation	P _T		154	W
単発アバランシェ電流 Single avalanche current	I _{AS}	開始 Tch=25°C Tch≤150°C Starting Tch=25°C Tch≤150°C	47	A
単発アバランシェエネルギー Single avalanche energy	E _{AS}	開始 Tch=25°C Tch≤150°C Starting Tch=25°C Tch≤150°C	258	mJ

Module

項目 Item	記号 Symbol	条件 Conditions	規格値 Ratings	単位 Unit
保存温度 Storage temperature	Tstg		-55~150	°C
締め付けトルク Mounting torque	TOR	固定ネジ M3 Fixing screw M3	0.8	N・m

Electrical Characteristics (Tc=25°C unless otherwise specified.)

MOSFET

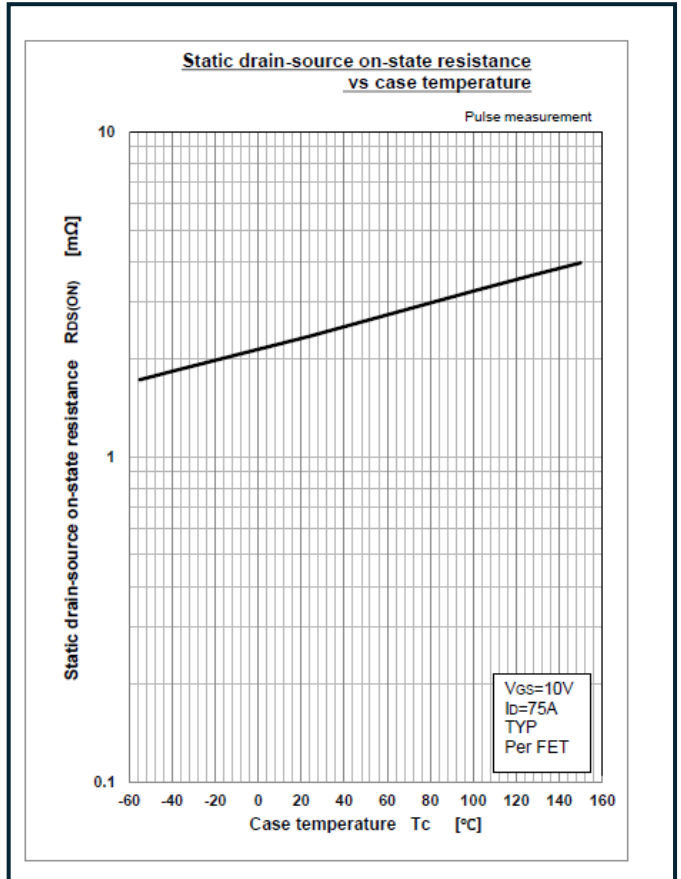
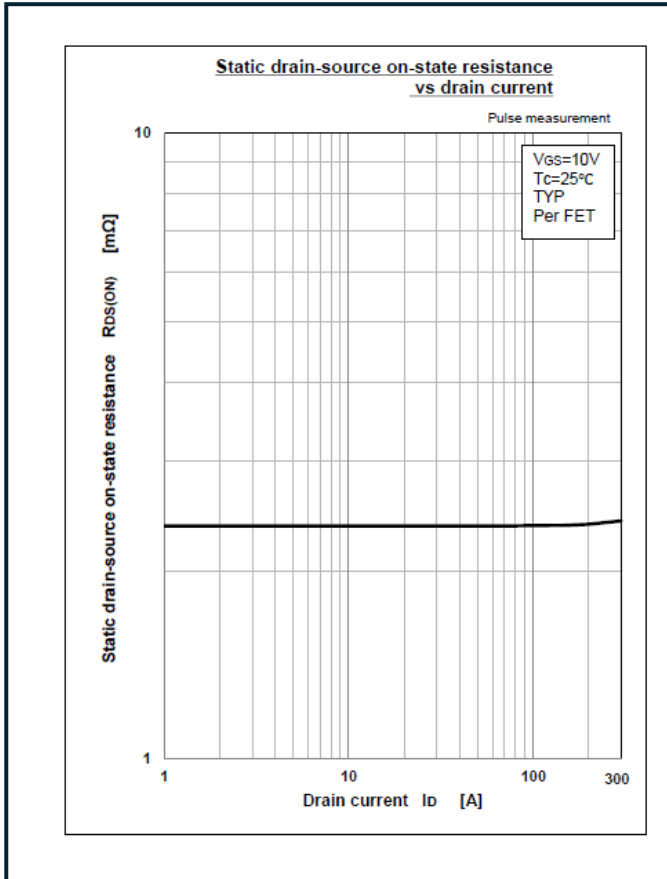
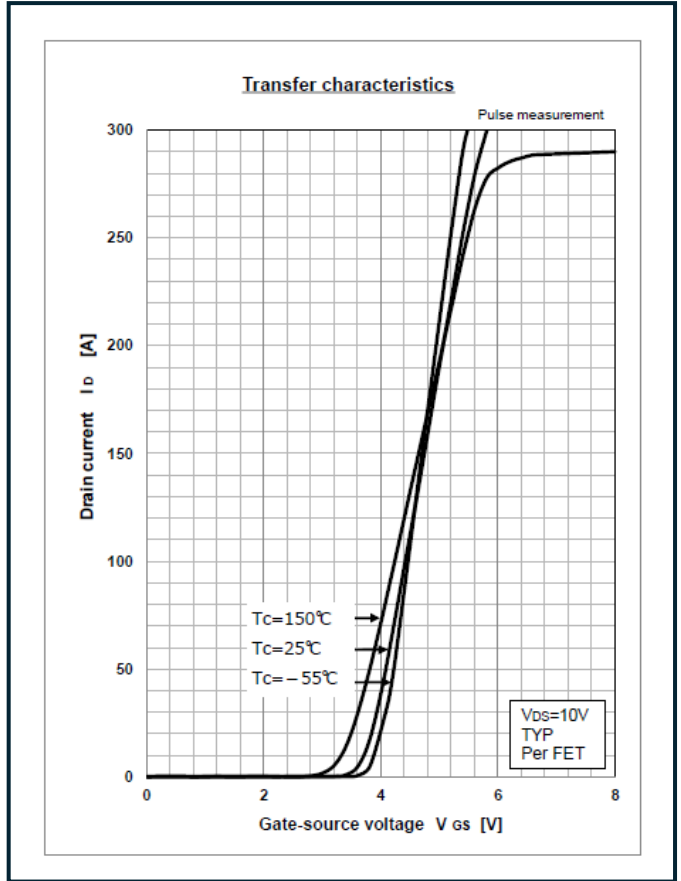
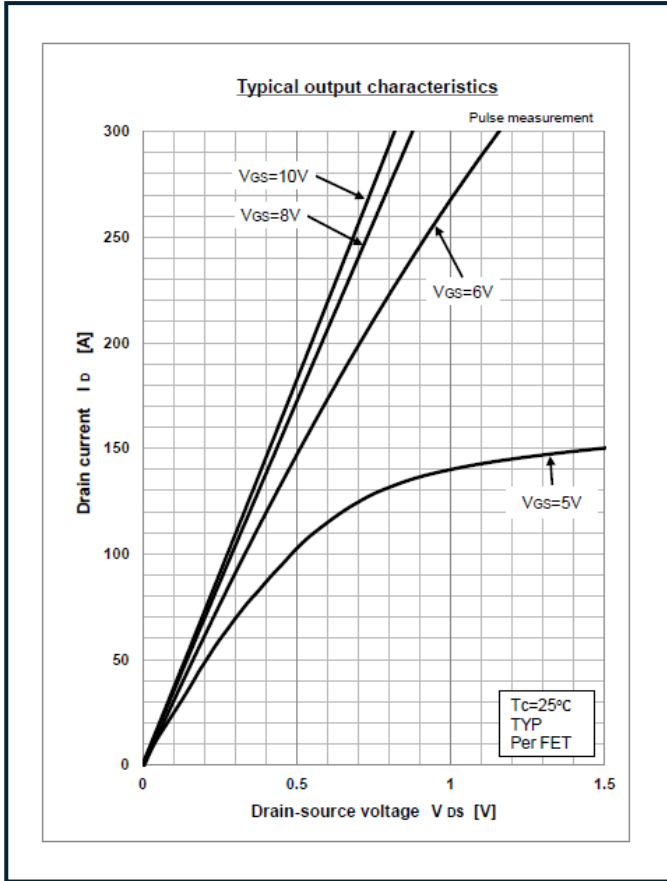
項目 Item	記号 Symbol	条件 Conditions		規格値 Ratings			単位 Unit
				Min.	Typ.	Max.	
ドレイン・ソース間降伏電圧 Drain-source breakdown voltage	$V_{(BR)DS}$	$I_D=1mA, V_{GS}=0V$		60	–	–	V
ドレイン遮断電流 Zero gate voltage drain current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$		–	–	1.0	μA
ゲート漏れ電流 Gate-source leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$		–	–	± 0.1	μA
ドレイン・ソース間オン抵抗 Static drain-source on-state resistance	$R_{DS(ON)}$	Chip	$I_D=75A, V_{GS}=10V$	–	1.86	–	m Ω
		Terminal	$I_D=75A, V_{GS}=10V$	–	2.36	2.95	m Ω
ゲートしきい値電圧 Gate threshold voltage	V_{TH}	$I_D=1mA, V_{DS}=10V$		2.0	3.0	4.0	V
ソース・ドレイン間ダイオード順電圧 Source-drain diode forward voltage	V_{SD}	$I_S=100A, V_{GS}=0V$		–	–	1.5	V
ゲート全電荷量 Total gate charge	Q_g	$V_{DD}=48V, V_{GS}=10V, I_D=100A$ (ディスクリートMOSFETデバイスの電気的 特性値) (Electrical characteristics of discrete MOSFET device)		–	72	–	nC
ゲート・ソース電荷量 Gate to source charge	Q_{gs}			–	21	–	
ゲート・ドレイン電荷量 Gate to drain charge	Q_{gd}			–	26	–	
入力容量 Input capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1MHz$ (ディスクリートMOSFETデバイスの電気的 特性値) (Electrical characteristics of discrete MOSFET device)		–	4800	–	pF
帰還容量 Reverse transfer capacitance	C_{rss}			–	160	–	
出力容量 Output capacitance	C_{oss}			–	2030	–	
ターンオン遅延時間 Turn-on delay time	$t_{d(on)}$	$I_D=50A, V_{DD}=30V,$ $R_L=0.6\Omega, R_g=0\Omega,$ $V_{GS(+)}=10V, V_{GS(-)}=0V$ (ディスクリートMOSFETデバイスの電気的 特性値) (Electrical characteristics of discrete MOSFET device)		–	12	–	ns
上昇時間 Rise time	t_r			–	58	–	
ターンオフ遅延時間 Turn-off delay time	$t_{d(off)}$			–	30	–	
降下時間 Fall time	t_f			–	12	–	
ソース・ドレイン間ダイオード逆回復時間 Source-drain diode reverse recovery time	t_{rr}	$I_F=100A, V_{GS}=0V, di/dt=-100A/\mu s$ (ディスクリートMOSFETデバイスの電気的 特性値) (Electrical characteristics of discrete MOSFET device)		–	63	–	ns
ソース・ドレイン間ダイオード逆回復電荷量 Source-drain diode reverse recovery charge	Q_{rr}			–	85	–	nC

Electrical Characteristics (Tc=25°C unless otherwise specified.)

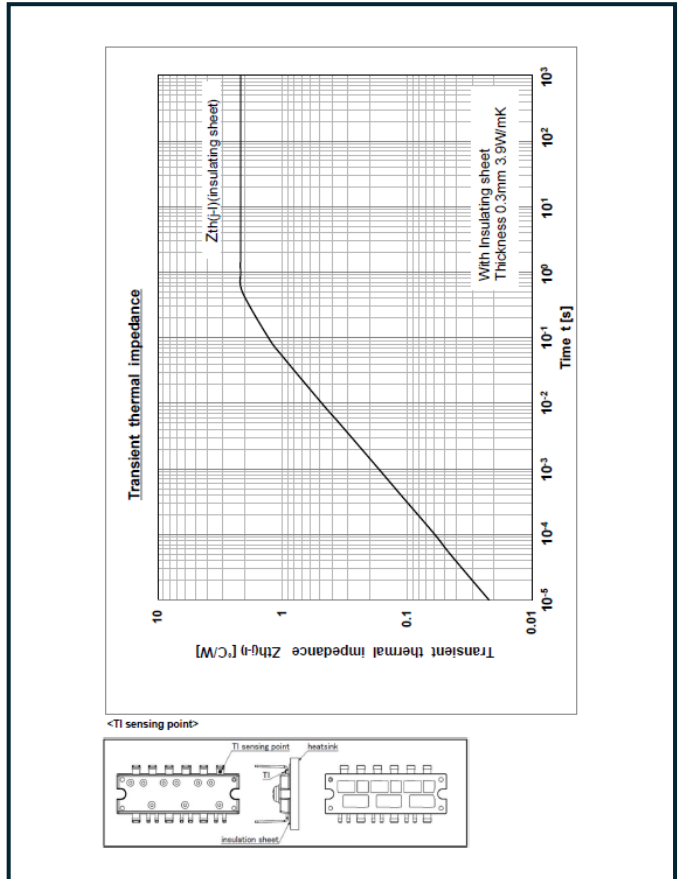
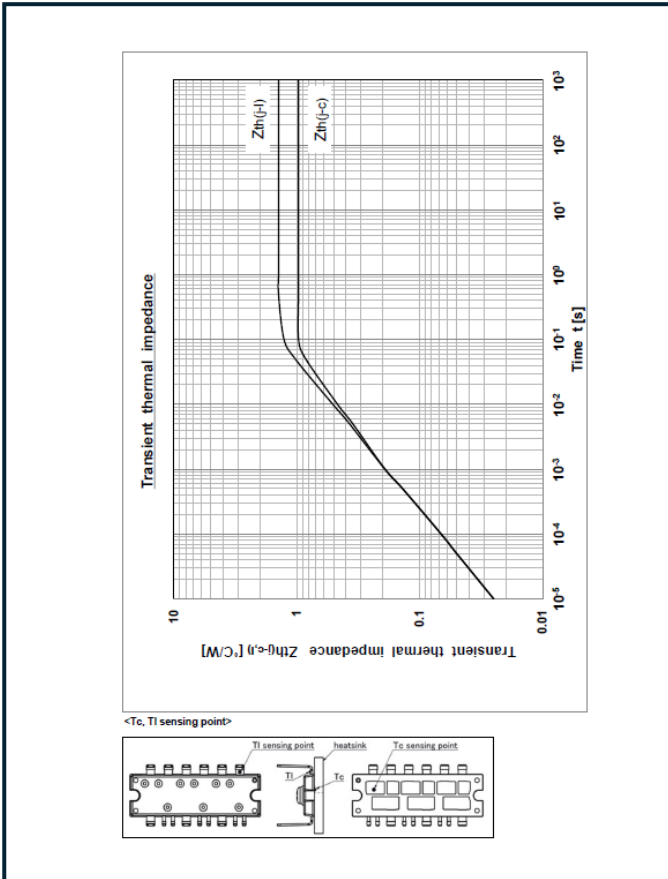
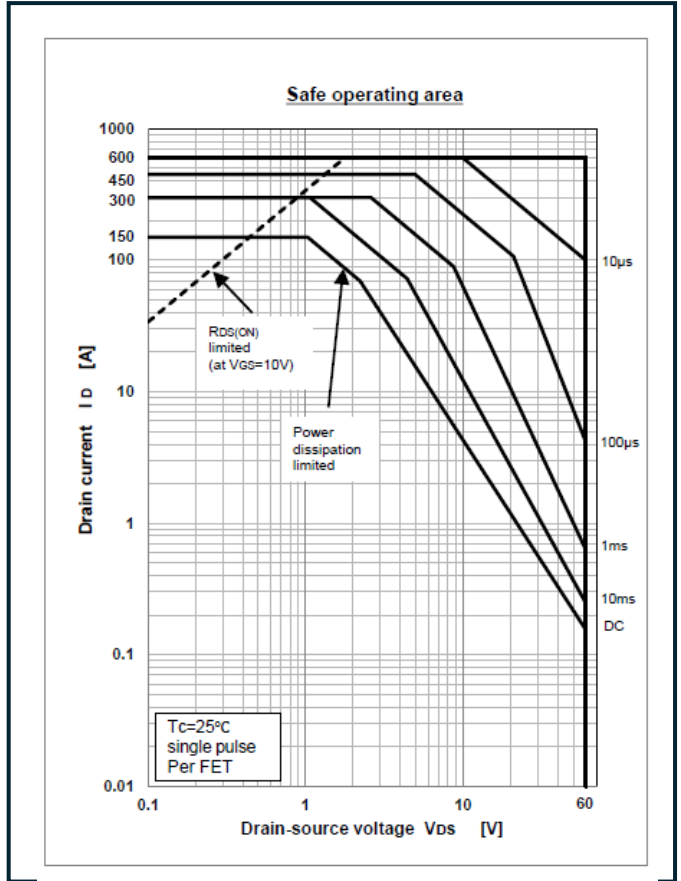
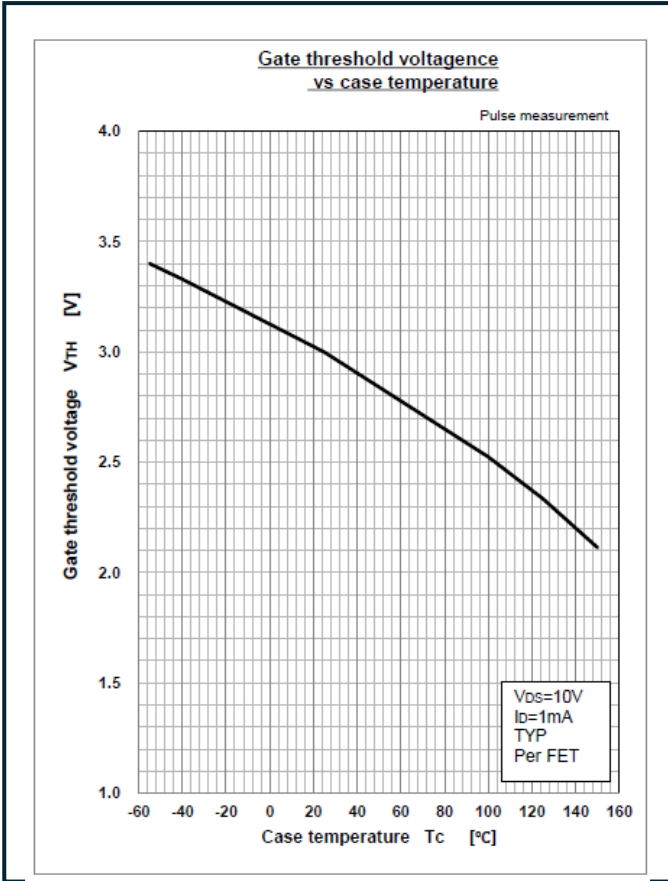
Module

項目 Item	記号 Symbol	条件 Conditions	規格値 Ratings			単位 Unit
			Min.	Typ.	Max.	
熱抵抗 Thermal resistance	$R_{th(j-c)}$	接合部・ケース間 Junction to case	—	—	0.97	°C/W
	$R_{th(j-l)}$	接合部・リード間 Junction to lead	—	—	1.41	
		接合部・リード間(絶縁シート), 厚さ 0.3 mm, 熱伝導率 3.9W/mK Junction to lead, With insulating sheet, Thickness 0.3mm, Thermal conductivity 3.9W/mK	—	—	2.16	

CHARACTERISTIC DIAGRAMS

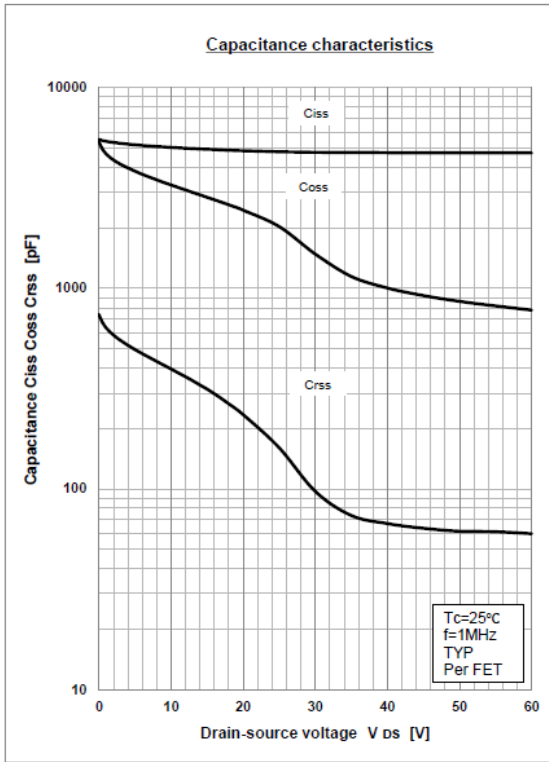


CHARACTERISTIC DIAGRAMS

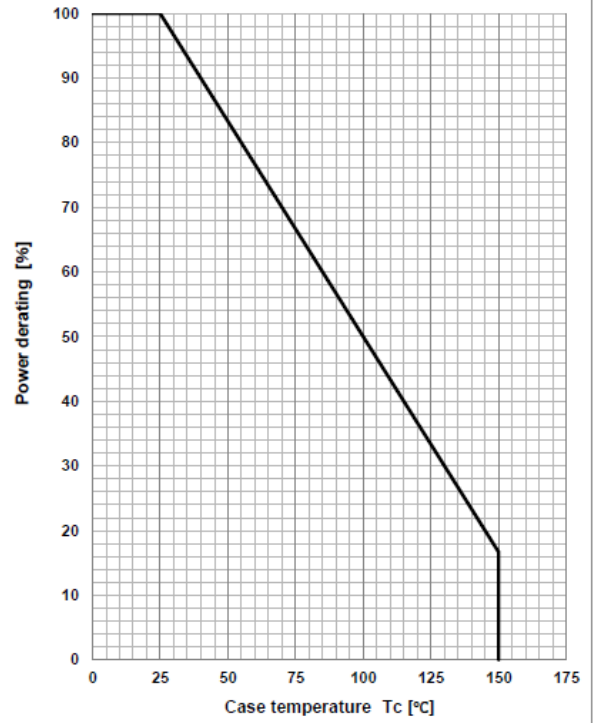


CHARACTERISTIC DIAGRAMS

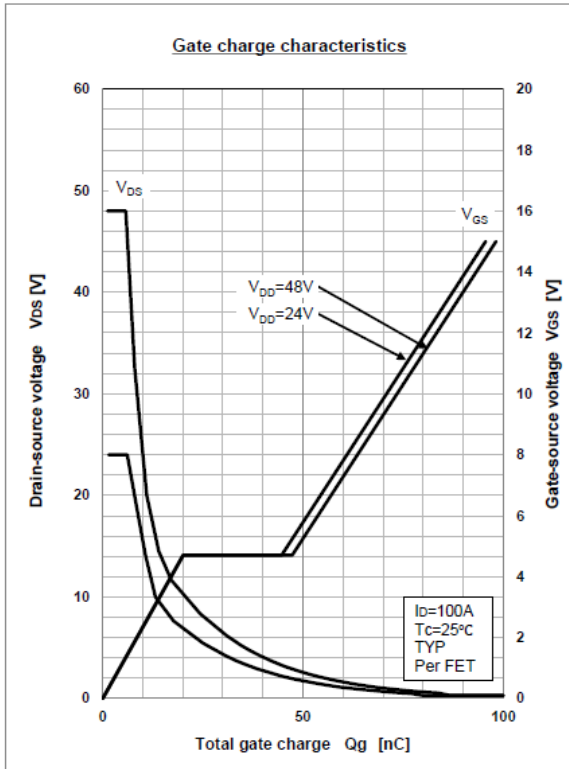
This figure shows the data of a discrete MOSFET device.



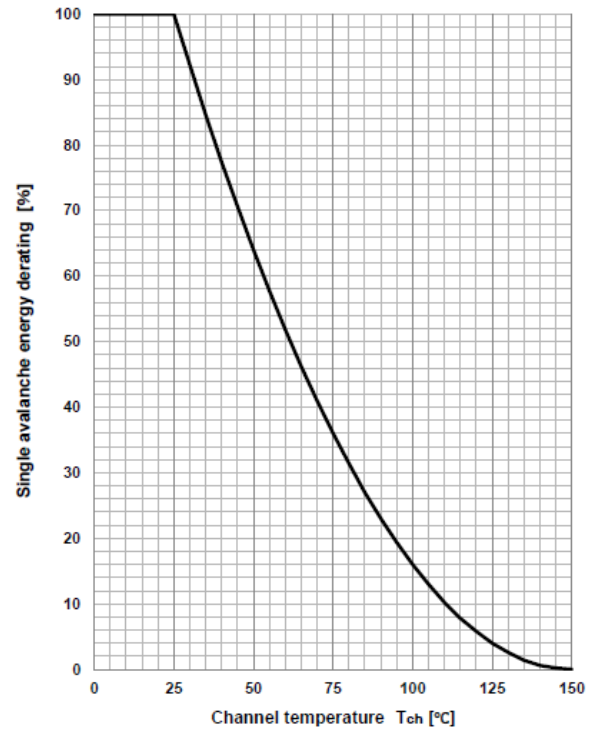
Power derating vs case temperature



This figure shows the data of a discrete MOSFET device.



Single avalanche energy derating vs channel temperature



Notes

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